

**Silicon PNP Power Transistor**

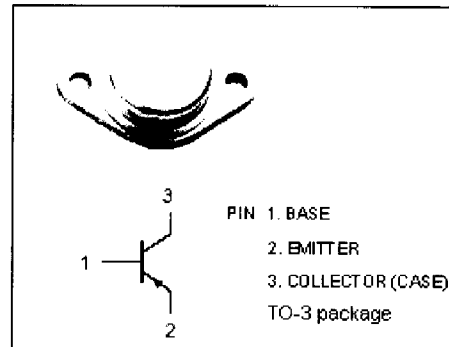
**2SA909**

**DESCRIPTION**

- High Power Dissipation-  
 :  $P_C = 150W(\text{Max.})@T_C=25^\circ\text{C}$
- Collector-Emitter Breakdown Voltage-  
 :  $V_{(BR)CEO} = -200V(\text{Min.})$
- Complement to Type 2SC1586

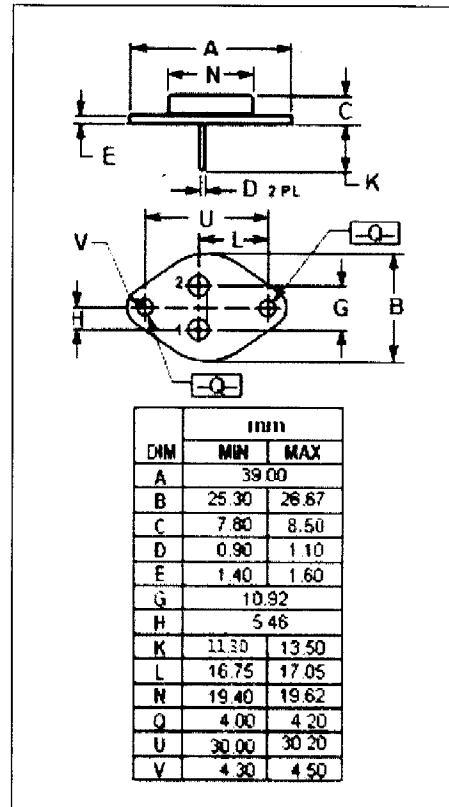
**APPLICATIONS**

- Designed for amplifier and general purpose applications.

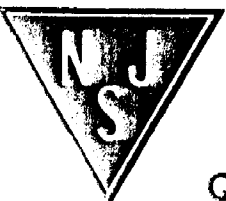


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-200	V
$V_{CEO}$	Collector-Emitter Voltage	-200	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current-Continuous	-15	A
$I_B$	Base Current-Continuous	-5	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	150	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-65~150	$^\circ\text{C}$



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**Silicon PNP Power Transistor****2SA909****ELECTRICAL CHARACTERISTICS****T<sub>j</sub>=25°C unless otherwise specified**

<b>SYMBOL</b>	<b>PARAMETER</b>	<b>CONDITIONS</b>	<b>MIN</b>	<b>TYP.</b>	<b>MAX</b>	<b>UNIT</b>
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}; I_B = 0$	-200			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -10\text{A}; I_B = -1\text{A}$			-3.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -200\text{V}; I_E = 0$			-1.0	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -6\text{V}; I_C = 0$			-1.0	mA
$h_{FE}$	DC Current Gain	$I_C = -5\text{A}; V_{CE} = -4\text{V}$	30			
$f_T$	Current-Gain—Bandwidth Product	$I_E = 0.5\text{A}; V_{CE} = -12\text{V}$		10		MHz